具有 Eco-Mode™ 的 4.5V 至 23V 输入，2A 同步降压 SWIFT™ 转换器

查询样品: TPS54239E

特性

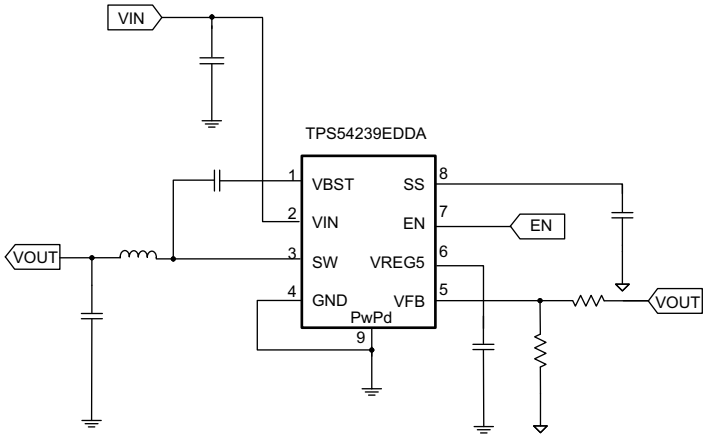
- **D-CAP2™** 模式支持快速瞬态响应
- 低输出纹波，支持陶瓷输出电容器
- 宽泛的 V_{IN}输入电压范围：**4.5V** 至 **23V**
- 输出电压范围：**0.76V** 至 **7.0V**
- 高效率集成型场效应晶体管 **(FET)**
  针对更低占空比应用进行了优化
  -140mΩ（高侧）与 **70mΩ** （低侧）
- 关断时的高效率，流耗不足 **10μA**
- 初始带隙参考的高精度
- 可调软启动
- 预偏置软启动
- **600kHz** 开关频率 **(f_{SW})**
- 逐周期限流
- 自动跳跃 **Eco-mode™** 为了在轻负载下实现高效率

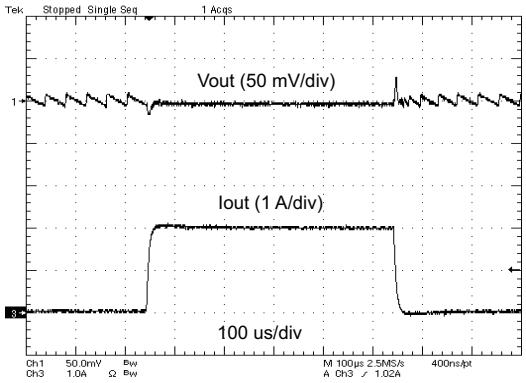
应用范围

- 低电压系统的广泛应用
  - 数字电视电源
  - 高清 **Blu-ray Disc™** 播放器
  - 网络家庭终端设备
  - 数字机顶盒 **(STB)**

说明

TPS54239E 是一款自适应接通时间 D-CAP2™ 模式同步降压转换器。 TPS54239E 可帮助系统设计人员通过一个低成本、低组件数、低待机电流解决方案来完成各种终端设备电源总线调节器集。 TPS54239E 的主控制环路采用 D-CAP2™ 模式控制，无需外部补偿组件便可实现极快的瞬态响应。 自适应接通时间控制支持较高负载状态下的脉宽调制 (PWM) 模式与轻负载下的 Eco-mode™ 工作模式之间的无缝转换。 Eco-mode™ 使 TPS54239 能够在较轻负载条件下保持高效率。 TPS54239E 的专有电路还有助于该器件适应诸如高分子有机半导体固体电容器 (POSCAP) 或特种聚合物电容器 (SP-CAP) 等低等效串联电阻 (ESR) 输出电容器以及超低 ESR 陶瓷电容器。 该器件的工作输入电压介于 4.5V 至 23V VIN 输入之间。 输出电压可在 0.76V 与 7V 之间进行设定。此外，该器件还特有一个可调软启动时间。 TPS54239E 采用 8 引脚 DDA 封装，并针对 -40°C 到 85°C 的工作温度范围内的运行而设计。





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

D-CAP2, Eco-mode are trademarks of Texas Instruments.
Blu-ray Disc is a trademark of Blu-ray Disc Association.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

Copyright © 2013, Texas Instruments Incorporated

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION(1)

T_A	PACKAGE(2) (3)	ORDERABLE PART NUMBER	PIN	TRANSPORT MEDIA
–40°C to 85°C	DDA	TPS54239EDDA	8	Tube
		TPS54239EDDAR		Tape and Reel

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(3) All package options have Cu NIPDAU lead/ball finish.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		VALUE		UNIT
		MIN	MAX	
Input voltage range	VIN, EN	–0.3	25	V
	VBST	–0.3	31	
	VBST (10 ns transient)	–0.3	33	
	VBST (vs SW)	–0.3	6.5	
	VFB, SS	–0.3	6.5	
	SW	–2	25	
	SW (10 ns transient)	–3	27	
Output voltage range	VREG5	–0.3	6.5	V
	GND	–0.3	0.3	
Voltage from GND to thermal pad, V_{diff}		–0.2	0.2	V
Electrostatic discharge	Human Body Model (HBM)		2	kV
	Charged Device Model (CDM)		500	V
Operating junction temperature, T_J		–40	150	°C
Storage temperature, T_{stg}		–55	150	

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

THERMAL METRIC(1)		TPS54239E DDA (8 PINS)	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	46.2	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance	53.9	
θ_{JB}	Junction-to-board thermal resistance	29.7	
ψ_{JT}	Junction-to-top characterization parameter	10.0	
ψ_{JB}	Junction-to-board characterization parameter	29.6	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	6.6	

(1) 有关传统和新的热 度量的更多信息，请参阅*IC 封装热度量*应用报告， SPRA953。

Copyright © 2013, Texas Instruments Incorporated

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range, (unless otherwise noted)

			MIN	MAX	UNIT
V_{IN}	Supply input voltage range		4.5	23	V
V_I	Input voltage range	VBST	–0.1	29	V
		VBST (10 ns transient)	–0.1	32	
		VBST(vs SW)	–0.1	5.7	
		SS	–0.1	5.7	
		EN	–0.1	23	
		VFB	–0.1	5.5	
		SW	–1.8	23	
		SW (10 ns transient)	–3	26	
		GND	–0.1	0.1	
V_O	Output voltage range	VREG5	–0.1	5.7	V
I_O	Output Current range	I_{VREG5}	0	10	mA
T_A	Operating free-air temperature		–40	85	°C
T_J	Operating junction temperature		–40	150	°C

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range, V_{IN} = 12 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
I_{VIN}	Operating - non-switching supply current	V_{IN} current, T_A = 25°C, EN = 5V, V_{FB} = 0.8V		600	1100	µA
I_{VINSDN}	Shutdown supply current	V_{IN} current, T_A = 25°C, EN = 0 V		3.0	10	µA
LOGIC THRESHOLD						
V_{ENH}	EN high-level input voltage	EN	1.6			V
V_{ENL}	EN low-level input voltage	EN			0.6	V
R_{EN}	EN pin resistance to GND	V_{EN} = 12 V	200	400	800	kΩ
V_{FB} VOLTAGE AND DISCHARGE RESISTANCE						
V_{FBTH}	V_{FB} threshold voltage	T_A = 25°C, V_O = 1.05 V, I_O = 10 mA, Eco-mode™ operation		772		mV
		T_A = 25°C, V_O = 1.05 V, continuous mode operation	749	765	781	mV
I_{VFB}	V_{FB} input current	V_{FB} = 0.8 V, T_A = 25°C		0	±0.1	µA
V_{REG5} OUTPUT						
V_{VREG5}	V_{REG5} output voltage	T_A = 25°C, 6.0 V < V_{IN} < 23 V, 0 < I_{VREG5} < 5 mA	5.2	5.5	5.7	V
I_{VREG5}	Output current	V_{IN} = 6 V, V_{REG5} = 4.0 V, T_A = 25°C	20			mA
MOSFET						
$R_{DS(on)h}$	High side switch resistance	25°C, V_{BST} - SW = 5.5 V(1)		140		mΩ
$R_{DS(on)l}$	Low side switch resistance	25°C(1)		70		mΩ
CURRENT LIMIT						
I_{ocl}	Current limit	L out = 2.2 µH(1)	2.5	3.1	4.6	A
THERMAL SHUTDOWN						
T_{SDN}	Thermal shutdown threshold	Shutdown temperature (1)		165		°C
		Hysteresis (1)		40		
ON-TIME TIMER CONTROL						
t_{ON}	On time	V_{IN} = 12 V, V_O = 1.05 V		160		ns
$t_{OFF(MIN)}$	Minimum off time	T_A = 25°C, V_{FB} = 0.7 V(1)		260	310	ns

(1) Not production tested.

Copyright © 2013, Texas Instruments Incorporated

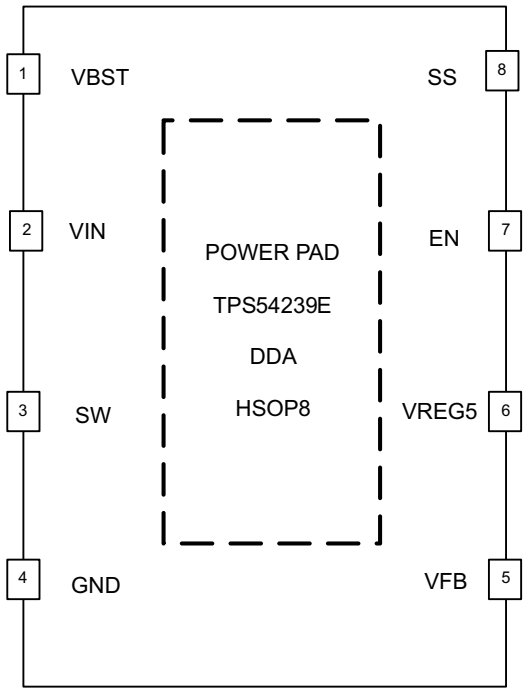
ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range, V_{IN} = 12 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SOFT START						
I_{SSC}	SS charge current	V_{SS} = 1.0 V	4.2	6.0	7.8	µA
I_{SSD}	SS discharge current	V_{SS} = 0.5 V	0.8	1.5		mA
HICCUP AND OVERVOLTAGE PROTECTION						
V_{OVP}	Output OVP threshold	OVP Detect (L>H)		125%		
V_{UVP}	Output Hiccup threshold	Hiccup detect (H>L)		65%		
T_{UVPDEL}	Output Hiccup delay	to Hiccup state		6		µs
T_{UVPEN}	Output Hiccup Enable delay	Relative to soft-start time		x1.7		
UVLO						
UVLO	UVLO threshold	Wake up V_{REG5} voltage	3.45	3.75	4.05	V
		Hysteresis V_{REG5} voltage	0.17	0.33	0.47	

DEVICE INFORMATION

DDA PACKAGE
(TOP VIEW)



PIN FUNCTIONS

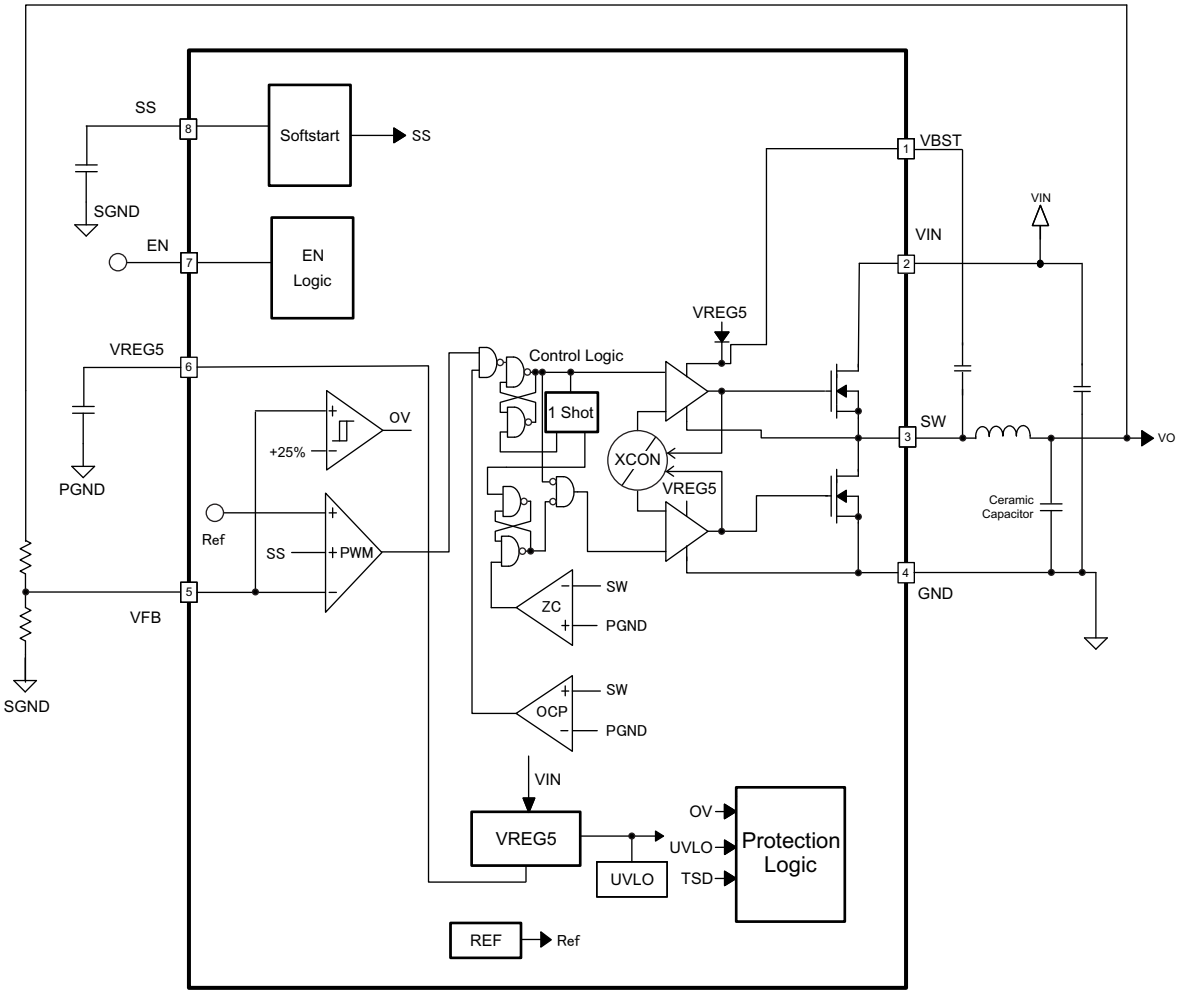
PIN		DESCRIPTION
NAME	NO.	
VBST	1	Supply input for the high-side FET gate drive circuit. Connect 0.1µF capacitor between VBST and SW pins. An internal diode is connected between VREG5 and VBST.
VIN	2	Input voltage supply pin.
SW	3	Switch node connection between high-side NFET and low-side NFET.
GND	4	Ground pin. Power ground return for switching circuit. Connect sensitive SS and VFB returns to GND at a single point.
VFB	5	Converter feedback input. Connect to output voltage with feedback resistor divider.

Copyright © 2013, Texas Instruments Incorporated

PIN FUNCTIONS (continued)

PIN		DESCRIPTION
NAME	NO.	
VREG5	6	5.5 V power supply output. A capacitor (typical 0.47 µF) should be connected to GND. VREG5 is not active when EN is low.
EN	7	Enable input control. EN is active high and must be pulled up to enable the device.
SS	8	Soft-start control. An external capacitor should be connected to GND.
Exposed Thermal Pad	Back side	Thermal pad of the package. Must be soldered to achieve appropriate dissipation. Must be connected to GND.

FUNCTIONAL BLOCK DIAGRAM



OVERVIEW

The TPS54239E is a 2-A synchronous step-down (buck) converter with two integrated N-channel MOSFETs. It operates using D-CAP2™ mode control. The fast transient response of D-CAP2™ control reduces the output capacitance required to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

DETAILED DESCRIPTION

PWM Operation

The main control loop of the TPS54239E is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2™ mode control. D-CAP2™ mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot is set by the converter input voltage, VIN, and the output voltage, VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2™ mode control.

PWM Frequency and Adaptive On-Time Control

TPS54239E uses an adaptive on-time control scheme and does not have a dedicated on board oscillator. The TPS54239E runs with a pseudo-constant frequency of 600 kHz by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage; therefore, when the duty ratio is VOUT/VIN, the frequency is constant.

Auto-Skip Eco-Mode™ Control

The TPS54239E is designed with Auto-Skip Eco-mode™ to increase light load efficiency. As the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to point that its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The rectifying MOSFET is turned off when its zero inductor current is detected. As the load current further decreases the converter run into discontinuous conduction mode. The on-time is kept almost the same as is was in the continuous conduction mode so that it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. The transition point to the light load operation $I_{OUT(LL)}$ current can be calculated in Equation 1

$$I_{OUT(LL)} = \frac{1}{2 \cdot L \cdot fsw} \cdot \frac{(V_{IN} - V_{OUT}) \cdot V_{OUT}}{V_{IN}} \quad (1)$$

Soft Start and Pre-Biased Soft Start

The soft start function is adjustable. When the EN pin becomes high, 6 µA current begins charging the capacitor which is connected from the SS pin to GND. Smooth control of the output voltage is maintained during start up. The equation for the slow start time is shown in Equation 2. VFB voltage is 0.765 V and SS pin source current is 6 µA.

$$t_{SS}(ms) = \frac{C_{SS}(nF) \times V_{REF} \times 1.1}{I_{SS}(\mu A)} = \frac{C_{SS}(nF) \times 0.765 \times 1.1}{6} \quad (2)$$

The TPS54239E contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than feedback voltage V_{FB}), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-by-cycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensure that the out voltage (V_O) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

Copyright © 2013, Texas Instruments Incorporated

Current Protection

The output overcurrent protection (OCP) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored by measuring the low-side FET switch voltage between the SW pin and GND. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

During the on time of the high-side FET switch, the switch current increases at a linear rate determined by V_{IN}, V_{OUT}, the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current Iout. The TPS54239E constantly monitors the low-side FET switch voltage, which is proportional to the switch current, during the low-side on-time. If the measured voltage is above the voltage proportional to the current limit, an internal counter is incremented per each SW cycle and the converter maintains the low-side switch on until the measured voltage is below the voltage corresponding to the current limit at which time the switching cycle is terminated and a new switching cycle begins. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner. If the over current condition exists for 7 consecutive switching cycles, the internal OCL threshold is set to a lower level, reducing the available output current. When a switching cycle occurs where the switch current is not above the lower OCL threshold, the counter is reset and the OCL limit is returned to the higher value.

There are some important considerations for this type of over-current protection. The load current one half of the peak-to-peak inductor current higher than the over-current threshold. Also when the current is being limited, the output voltage tends to fall as the demanded load current may be higher than the current available from the converter. This may cause the output voltage to fall. When the VFB voltage becomes lower than 65% of the target voltage, the UVP comparator detects it. After 6μs detecting the UVP voltage, device will shut down and re-start after 7 times SS period for Hiccup.

When the over current condition is removed, the output voltage returns to the regulated value. This protection is non-latching.

Over Voltage Protection

TPS54239E detects over voltage conditions by monitoring the feedback voltage (VFB). This function is enabled after approximately 1.7 x times the soft start time.

When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and both the high-side MOSFET driver and the low-side MOSFET driver turn off. This function is non-latch operation.

UVLO Protection

Undervoltage lock out protection (UVLO) monitors the voltage of the V_{REG5} pin. When the V_{REG5} voltage is lower than UVLO threshold voltage, the TPS54239E is shut off. This protection is non-latching.

Thermal Shutdown

TPS54239E monitors the temperature of itself. If the temperature exceeds the threshold value (typically 165°C), the device is shut off. This is non-latch protection.

Copyright © 2013, Texas Instruments Incorporated

TYPICAL CHARACTERISTICS

VIN = 12 V, T_A = 25°C (unless otherwise noted).

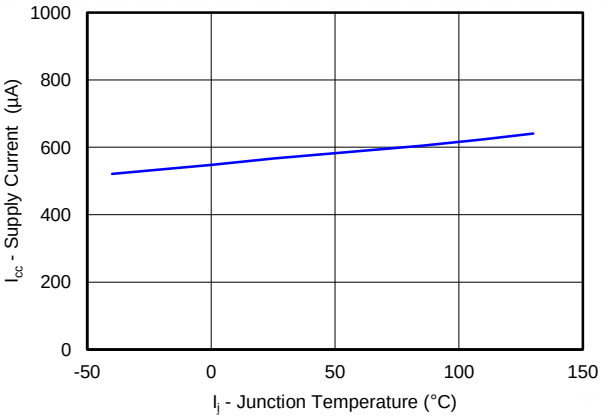


Figure 1. VIN CURRENT vs JUNCTION TEMPERATURE

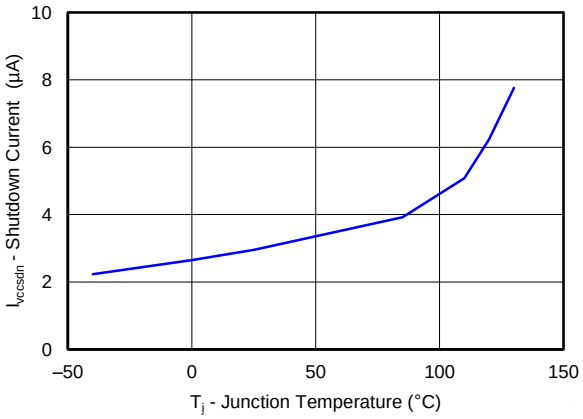


Figure 2. VIN SHUTDOWN CURRENT vs JUNCTION TEMPERATURE

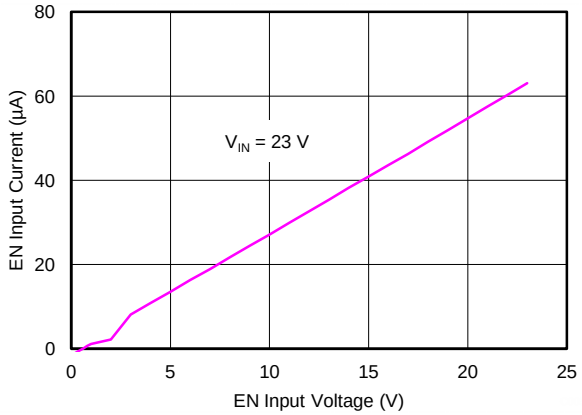


Figure 3. EN CURRENT vs EN VOLTAGE

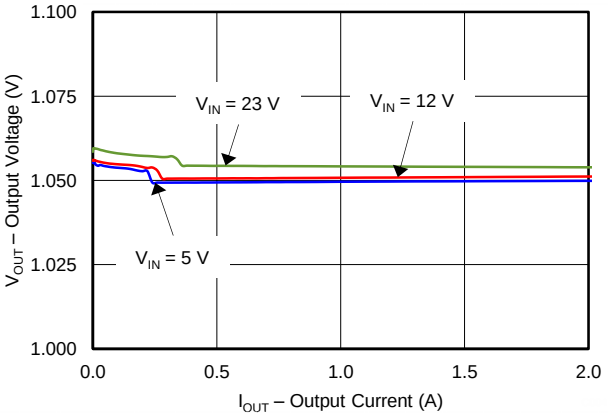


Figure 4. 1.05-V OUTPUT VOLTAGE vs OUTPUT CURRENT

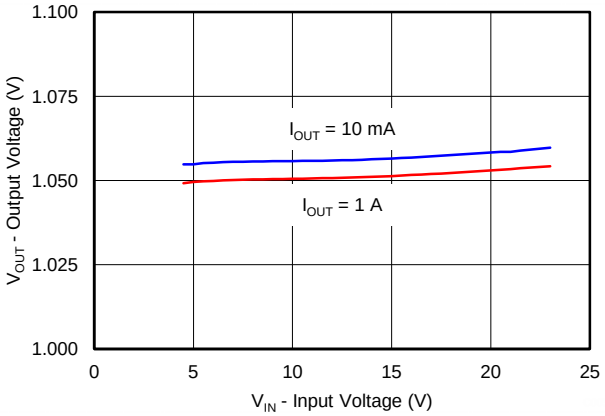


Figure 5. 1.05-V OUTPUT VOLTAGE vs INPUT VOLTAGE

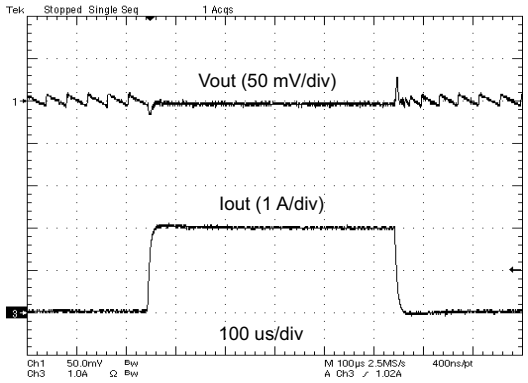


Figure 6. 1.05-V, LOAD TRANSIENT RESPONSE

Copyright © 2013, Texas Instruments Incorporated

TYPICAL CHARACTERISTICS

VIN = 12 V, T_A = 25°C (unless otherwise noted).

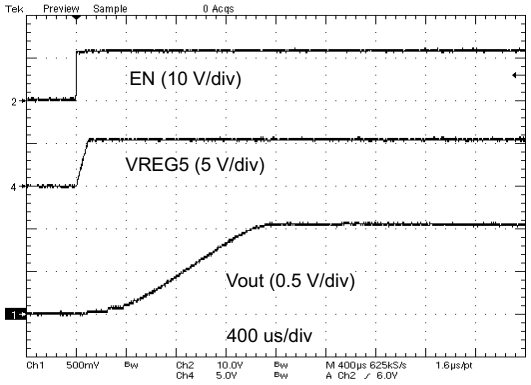


Figure 7. START-UP WAVE FORM

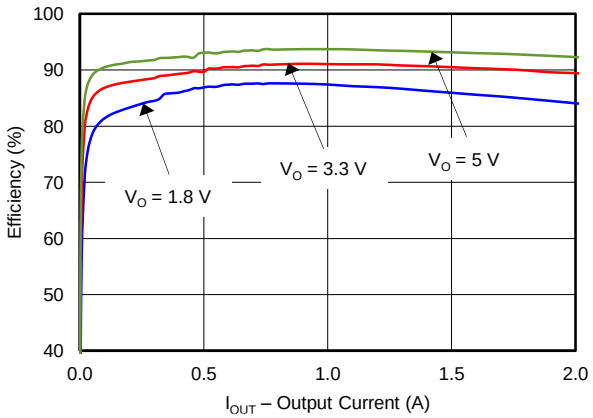


Figure 8. EFFICIENCY vs OUTPUT CURRENT

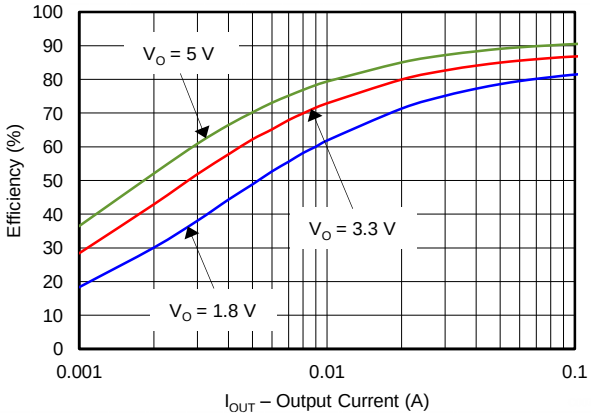


Figure 9. LIGHT LOAD EFFICIENCY vs OUTPUT CURRENT

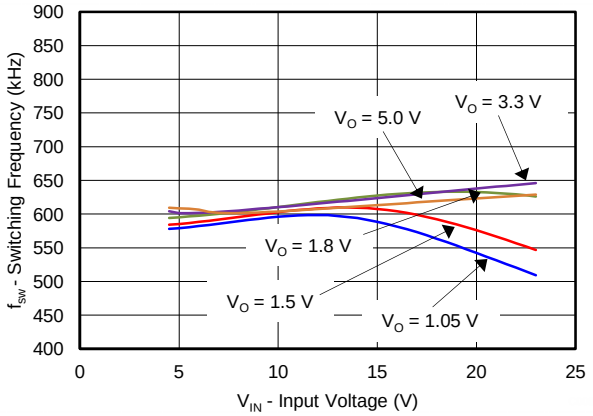


Figure 10. SWITCHING FREQUENCY vs INPUT VOLTAGE (I_O = 1 A)

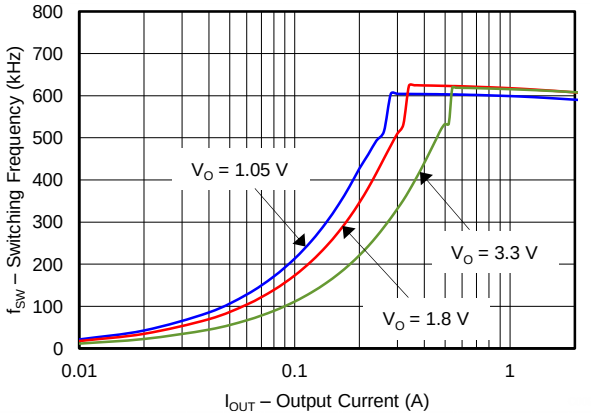


Figure 11. SWITCHING FREQUENCY vs OUTPUT CURRENT

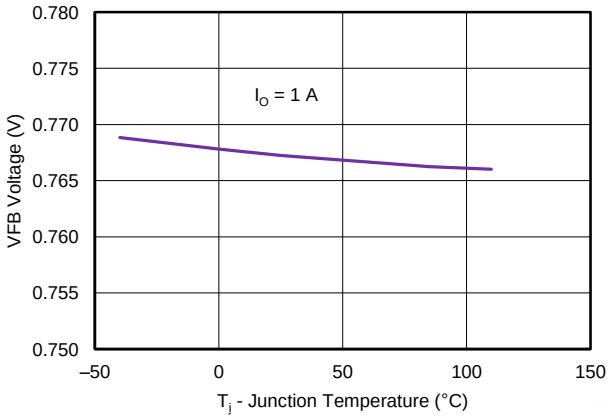


Figure 12. VFB VOLTAGE vs JUNCTION TEMPERATURE (I_O = 1 A)

Copyright © 2013, Texas Instruments Incorporated

TYPICAL CHARACTERISTICS (continued)

VIN = 12 V, T_A = 25°C (unless otherwise noted).

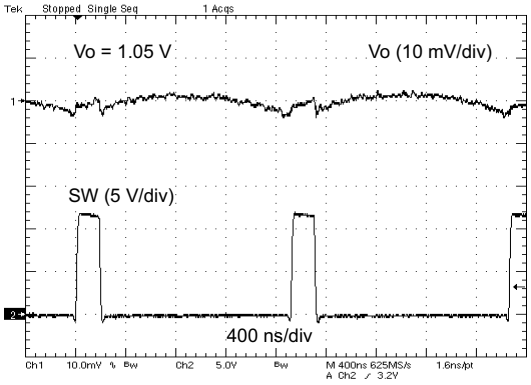


Figure 13. VOLTAGE RIPPLE AT OUTPUT (I_O = 2A)

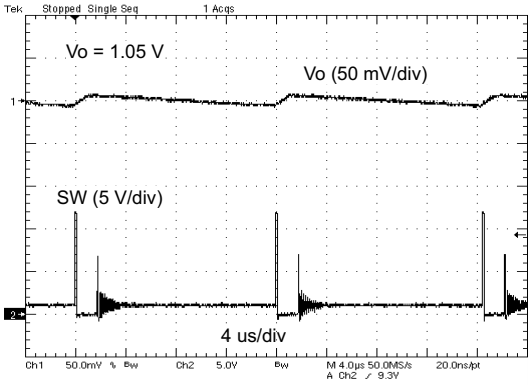


Figure 14. VOLTAGE RIPPLE AT OUTPUT (I_O = 30 mA)

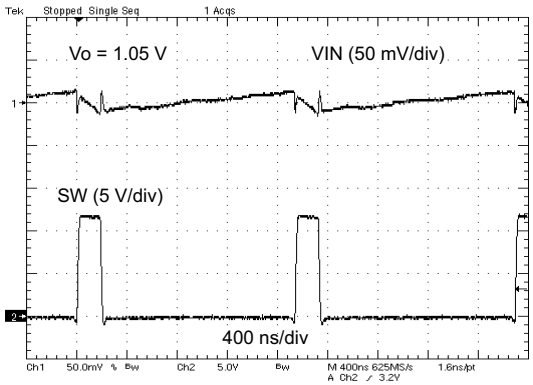


Figure 15. VOLTAGE RIPPLE AT INPUT (I_O = 2 A)

Copyright © 2013, Texas Instruments Incorporated

DESIGN GUIDE

Step-By-Step Design Procedure

To begin the design process, the user must know a few application parameters:

- Input voltage range
- Output voltage
- Output current
- Output voltage ripple
- Input voltage ripple

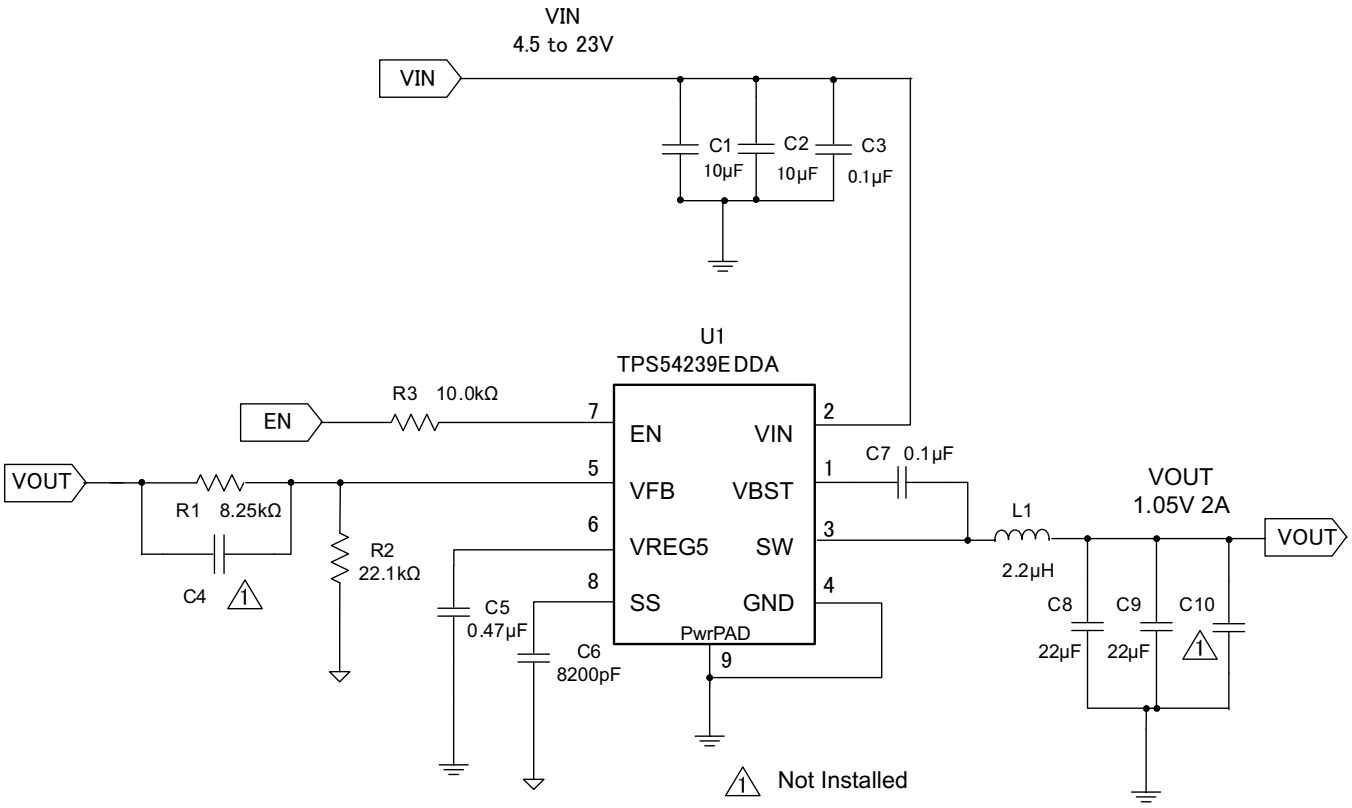


Figure 16. Shows the schematic diagram for this design example.

Output Voltage Resistors Selection

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using Equation 3 to calculate V_{OUT}.

To improve efficiency at light loads consider using larger value resistors, high resistance is more susceptible to noise, and the voltage errors from the VFB input current are more noticeable.

$$V_{OUT} = 0.765 \times \left(1 + \frac{R1}{R2}\right) \quad (3)$$

Output Filter Selection

The output filter used with the TPS54239E is an LC circuit. This LC filter has double pole at:

$$F_P = \frac{1}{2\pi\sqrt{L_{OUT} \times C_{OUT}}} \quad (4)$$

Copyright © 2013, Texas Instruments Incorporated

At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the TPS54239E. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a –40 dB per decade rate and the phase drops rapidly. D-CAP2™ introduces a high frequency zero that reduces the gain roll off to –20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor selected for the output filter must be selected so that the double pole of Equation 4 is located below the high frequency zero but close enough that the phase boost provided be the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in Table 1

Table 1. Recommended Component Values

Output Voltage (V)	R1 (kΩ)	R2 (kΩ)	C4 (pF)(1)			L1 (µH)			C8 + C9 + C10 (µF)	
			Min	Typ	Max	Min	Typ	Max	Min	Max
1	6.81	22.1	5	150	220	1.5	2.2	4.7	22	68
1.05	8.25	22.1	5	150	220	1.5	2.2	4.7	22	68
1.2	12.7	22.1	5		100	1.5	2.2	4.7	22	68
1.5	21.5	22.1	5		68	1.5	2.2	4.7	22	68
1.8	30.1	22.1	5		22	2.2	3.3	4.7	22	68
2.5	49.9	22.1	5		22	2.2	3.3	4.7	22	68
3.3	73.2	22.1	5		22	2.2	3.3	4.7	22	68
5	124	22.1	5		22	3.3		4.7	22	68
6.5	165	22.1	5		22	3.3		4.7	22	68

(1) Optional

Since the DC gain is dependent on the output voltage, the required inductor value increases as the output voltage increases. Additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1. The amount of available phase boost is dependent on the output voltage. Higher output voltages will allow greater phase boost.

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 5, Equation 6 and Equation 7. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 600 kHz for f_{SW}.

Use 600 kHz for f_{SW}. Make sure the chosen inductor is rated for the peak current of Equation 6 and the RMS current of Equation 7.

$$II_{P-P} = \frac{V_{OUT}}{V_{IN(MAX)}} \times \frac{V_{IN(MAX)} - V_{OUT}}{L_O \times f_{SW}} \quad (5)$$

$$II_{PEAK} = I_O + \frac{II_{P-P}}{2} \quad (6)$$

$$I_{LO(RMS)} = \sqrt{I_O^2 + \frac{1}{12} II_{P-P}^2} \quad (7)$$

For this design example, the calculated peak current is 2.38 A and the calculated RMS current is 2.01 A. The inductor used is a TDK CLF7045T-2R2N with a peak current rating of 5.5 A and an RMS current rating of 4.3 A. For high current designs, TDK SPM6530T-4R7M 4.7µH is also recommended. The SPM6530 series has a higher current rating than the CLF7045 series.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS54239E is intended for use with ceramic or other low ESR capacitors. Recommended values range from 22µF to 68µF. Use Equation 8 to determine the required RMS current rating for the output capacitor.

$$I_{Co(RMS)} = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{\sqrt{12} \times V_{IN} \times L_O \times f_{SW}} \quad (8)$$

For this design two TDK C3216X5R0J226M 22µF output capacitors are used. The typical ESR is 2 mΩ each. The calculated RMS current is 0.22 A and each output capacitor is rated for 4A.

Copyright © 2013, Texas Instruments Incorporated

Input Capacitor Selection

The TPS54239E requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10 µF is recommended for the decoupling capacitor. An additional 0.1 µF capacitor from pin 2 to ground is optional to provide additional high frequency filtering. The capacitor voltage rating needs to be greater than the maximum input voltage.

Bootstrap Capacitor Selection

A 0.1 µF. ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.

VREG5 Capacitor Selection

A 0.47 µF. ceramic capacitor must be connected between the VREG5 to GND pin for proper operation. It is recommended to use a ceramic capacitor.

THERMAL INFORMATION

This 8-pin DDA package incorporates an exposed thermal pad that is designed to be directly to an external heartsick. The thermal pad must be soldered directly to the printed board (PCB). After soldering, the PCB can be used as a heartsick. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heartsick structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the exposed thermal pad and how to use the advantage of its heat dissipating abilities, see the Technical Brief, PowerPAD™ Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD™ Made Easy, Texas Instruments Literature No. SLMA004.

The exposed thermal pad dimensions for this package are shown in the following illustration.

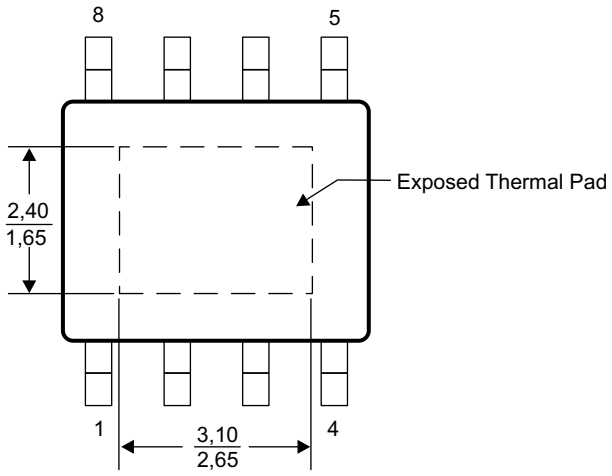


Figure 17. Thermal Pad Dimensions

Copyright © 2013, Texas Instruments Incorporated

LAYOUT CONSIDERATIONS

1. Keep the input switching current loop as small as possible.
2. Keep the SW node as physically small and short as possible to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin of the device.
3. Keep analog and non-switching components away from switching components.
4. Make a single point connection from the analog ground to power ground.
5. Do not allow switching current to flow under the device.
6. Keep the pattern lines for VIN and PGND broad.
7. Exposed pad of device must be connected to PGND with solder.
8. VREG5 capacitor should be placed near the device, and connected to PGND.
9. Output capacitor should be connected to a broad pattern of the PGND.
10. Voltage feedback loop should be as short as possible, and preferably with ground shield.
11. Lower resistor of the voltage divider which is connected to the VFB pin should be tied to analog ground trace.
12. Providing sufficient via is preferable for VIN, SW and PGND connection.
13. VIN input bypass capacitor and VIN high frequency bypass capacitor must be placed as near as possible to the device.
14. Performance based on four layer printed circuit board.

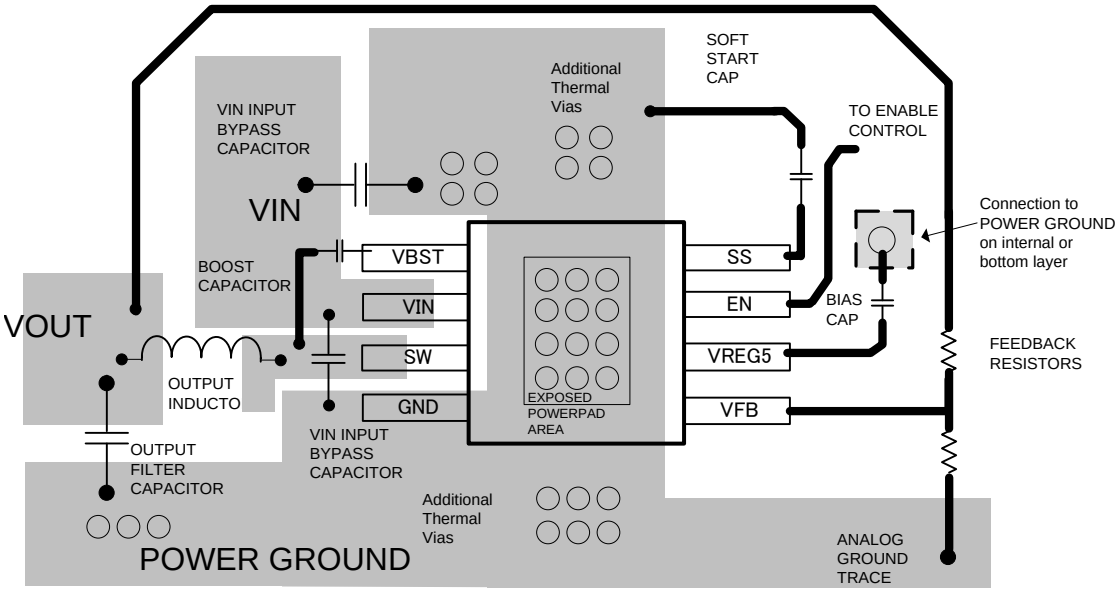


Figure 18. PCB Layout

Copyright © 2013, Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS54239EDDA	ACTIVE	SO PowerPAD	DDA	8	75	Green (RoHS & no Sb/Br)	CU SN	Level-2-260C-1 YEAR	-40 to 85	54239E	Samples
TPS54239EDDAR	ACTIVE	SO PowerPAD	DDA	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-2-260C-1 YEAR	-40 to 85	54239E	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

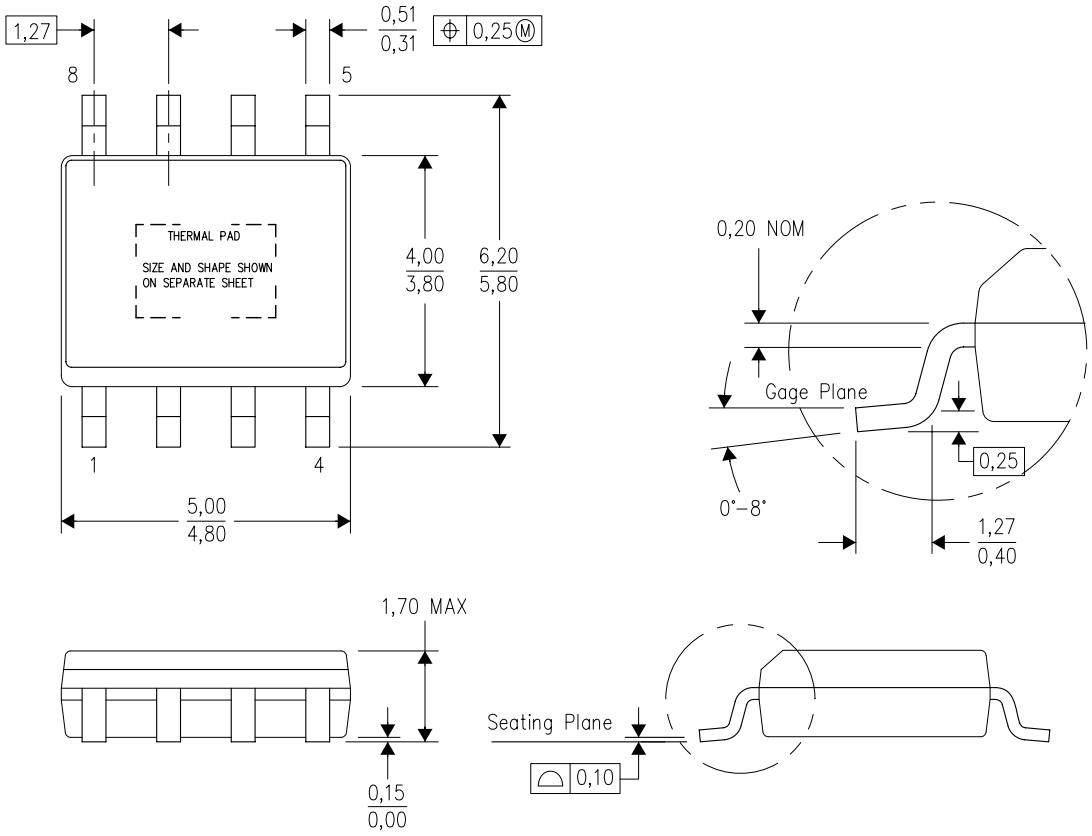
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL–OUTLINE



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http://www.ti.com>.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. This package complies to JEDEC MS–012 variation BA

PowerPAD is a trademark of Texas Instruments.

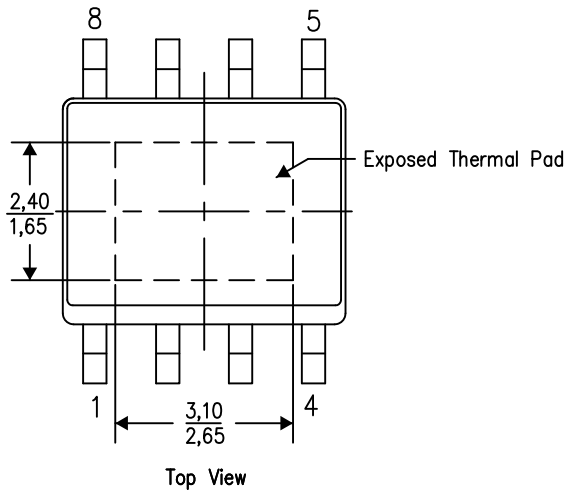
DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



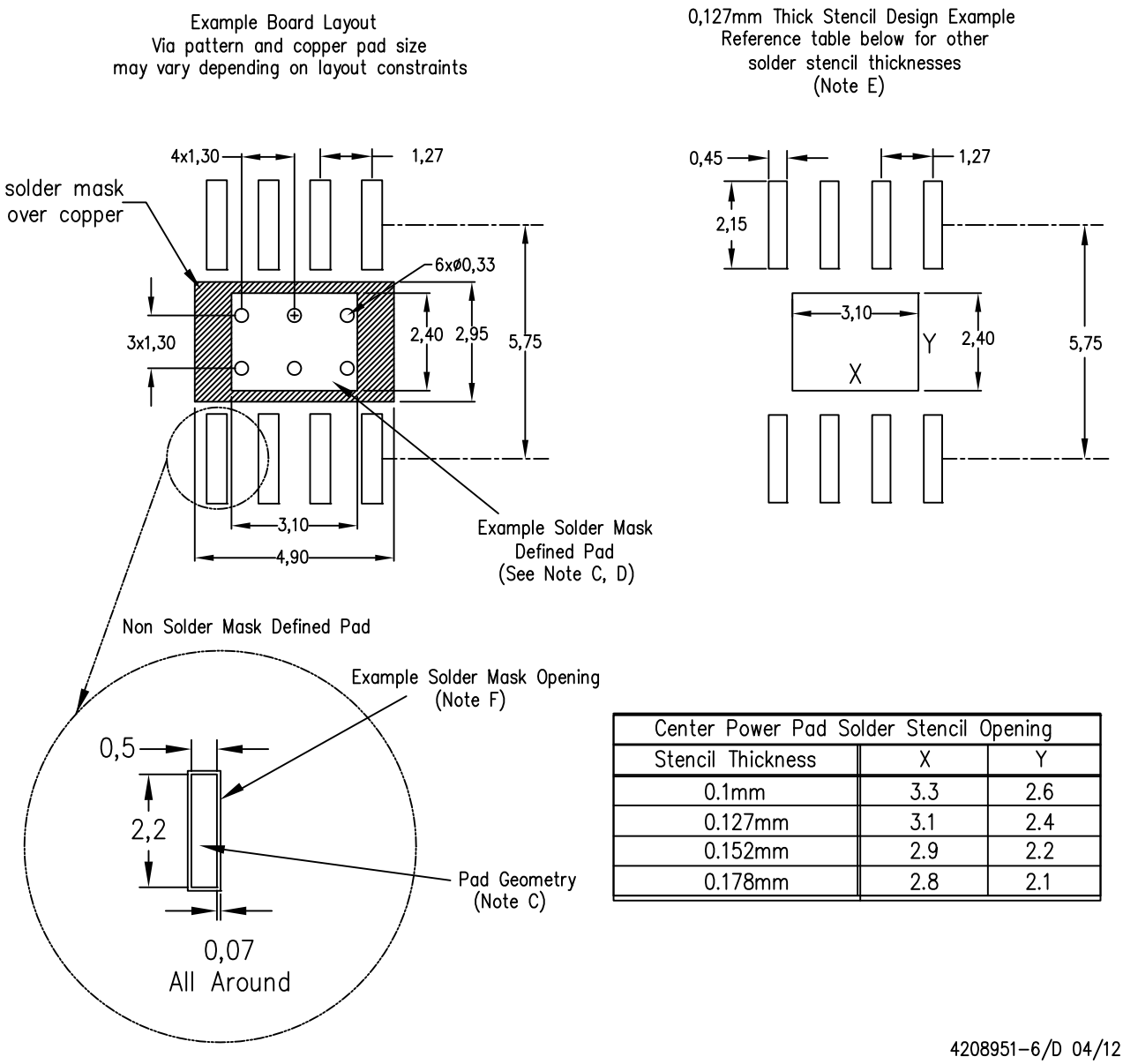
Exposed Thermal Pad Dimensions

4206322–6/L 05/12

NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments

DDA (R–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE



Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	3.3	2.6
0.127mm	3.1	2.4
0.152mm	2.9	2.2
0.178mm	2.8	2.1

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.
F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PowerPAD is a trademark of Texas Instruments.

重要声明

德州仪器(TI) 及其下属子公司有权根据 JESD46 最新标准, 对所提供的产品和服务进行更正、修改、增强、改进或其它更改， 并有权根据 JESD48 最新标准中止提供任何产品和服务。客户在下订单前应获取最新的相关信息, 并验证这些信息是否完整且是最新的。所有产品的销售都遵循在订单确认时所提供的TI 销售条款与条件。

TI 保证其所销售的组件的性能符合产品销售时 TI 半导体产品销售条件与条款的适用规范。仅在 TI 保证的范围内，且 TI 认为 有必要时才会使用测试或其它质量控制技术。除非适用法律做出了硬性规定，否则没有必要对每种组件的所有参数进行测试。

TI 对应用帮助或客户产品设计不承担任何义务。客户应对其使用 TI 组件的产品和应用自行负责。为尽量减小与客户产品和应 用相关的风险，客户应提供充分的设计与操作安全措施。

TI 不对任何 TI 专利权、版权、屏蔽作品权或其它与使用了 TI 组件或服务的组合设备、机器或流程相关的 TI 知识产权中授予 的直接或隐含权限作出任何保证或解释。TI 所发布的与第三方产品或服务有关的信息，不能构成从 TI 获得使用这些产品或服 务的许可、授权、或认可。使用此类信息可能需要获得第三方的专利权或其它知识产权方面的许可，或是 TI 的专利权或其它 知识产权方面的许可。

对于 TI 的产品手册或数据表中 TI 信息的重要部分，仅在没有对内容进行任何篡改且带有相关授权、条件、限制和声明的情况 下才允许进行复制。TI 对此类篡改过的文件不承担任何责任或义务。复制第三方的信息可能需要服从额外的限制条件。

在转售 TI 组件或服务时，如果对该组件或服务参数的陈述与 TI 标明的参数相比存在差异或虚假成分，则会失去相关 TI 组件 或服务的所有明示或暗示授权，且这是不正当的、欺诈性商业行为。TI 对任何此类虚假陈述均不承担任何责任或义务。

客户认可并同意，尽管任何应用相关信息或支持仍可能由 TI 提供，但他们将独力负责满足与其产品及在其应用中使用 TI 产品 相关的所有法律、法规和安全相关要求。客户声明并同意，他们具备制定与实施安全措施所需的全部专业技术和知识，可预见 故障的危险后果、监测故障及其后果、降低有可能造成人身伤害的故障的发生机率并采取适当的补救措施。客户将全额赔偿因 在此类安全关键应用中使用任何 TI 组件而对 TI 及其代理造成的任何损失。

在某些场合中，为了推进安全相关应用有可能对 TI 组件进行特别的促销。TI 的目标是利用此类组件帮助客户设计和创立其特 有的可满足适用的功能安全性标准和要求的终端产品解决方案。尽管如此，此类组件仍然服从这些条款。

TI 组件未获得用于 FDA Class III（或类似的生命攸关医疗设备）的授权许可，除非各方授权官员已经达成了专门管控此类使 用的特别协议。

只有那些 TI 特别注明属于军用等级或“增强型塑料”的 TI 组件才是设计或专门用于军事/航空应用或环境的。购买者认可并同 意，对并非指定面向军事或航空航天用途的 TI 组件进行军事或航空航天方面的应用，其风险由客户单独承担，并且由客户独 力负责满足与此类使用相关的所有法律和法规要求。

TI 已明确指定符合 ISO/TS16949 要求的产品，这些产品主要用于汽车。在任何情况下，因使用非指定产品而无法达到 ISO/TS16949 要求，TI不承担任何责任。

	产品		应用
数字音频	www.ti.com.cn/audio	通信与电信	www.ti.com.cn/telecom
放大器和线性器件	www.ti.com.cn/amplifiers	计算机及周边	www.ti.com.cn/computer
数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
时钟和计时器	www.ti.com.cn/clockandtimers	医疗电子	www.ti.com.cn/medical
接口	www.ti.com.cn/interface	安防应用	www.ti.com.cn/security
逻辑	www.ti.com.cn/logic	汽车电子	www.ti.com.cn/automotive
电源管理	www.ti.com.cn/power	视频和影像	www.ti.com.cn/video
微控制器 (MCU)	www.ti.com.cn/microcontrollers		
RFID 系统	www.ti.com.cn/rfidsys		
OMAP应用处理器	www.ti.com/omap		
无线连通性	www.ti.com.cn/wirelessconnectivity	德州仪器在线技术支持社区	www.deyisupport.com

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2016, Texas Instruments Incorporated